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LIST OF REFERENCES CITED BY APPLICANT

ATTY DOCKET NO.	SERIAL NO.
239525US2	10/603,771
APPLICANT	
Yukio TANIGUCHI, et al.	
FILING DATE	GROUP
June 26, 2003	2812

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
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☐ Additional References sheet(s) attached

Examiner

Date Considered 3/18/05

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO 1449 (Modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY DOCKET NO. 239525US2	SERIAL NO. New Application
LIST OF REFERENCES CITED BY APPLICANT	APPLICANT Yukio TANIGUCHI, et al.	
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☐ *Additional References sheet(s) attached*

Examiner	Date Considered 3/18/06

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